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Title: Recent Developments in Terahertz Metamaterials

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Seminar @ Zhejiang University
Hangzhou, China; 06/24/2011



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Recent Developments in Terahertz Metamaterials

Hou-Tong Chen

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Abstract

Metamaterials are a new class of man-made effective media that exhibit exotic electromagnetic properties which are difficult or impossible in naturally occurring materials. It is most likely that practical application of metamaterials will first happen in the underdeveloped THz frequency range. In this talk I will present a few recent developments in THz metamaterials from our group at LANL, which include: 1) actively and dynamically switchable and tunable hybrid THz metamaterials incorporated with semiconductors; 2) thermally and optically tunable high temperature superconducting THz metamaterials; and 3) metamaterial antireflection and perfect absorption. Both the experimental results and underlying mechanism will be presented.

Recent Developments in Terahertz Metamaterials

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*2011 International Symposium on
Microwave/Terahertz Science and Applications
Nanjing, China*



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Outline

- ☐ Introduction
- ☐ Actively and dynamically tunable THz metamaterials
 - Hybrid semiconductor metamaterials
 - Tuning through photoexcitation, voltage, temperature
 - Device applications
- ☐ High temperature superconducting metamaterials
 - Temperature tuning
 - Optical tuning
 - Theoretical investigation
- ☐ Metamaterials as surface coatings
 - Antireflection coatings
 - Perfect absorbers
 - Theory
- ☐ Summary



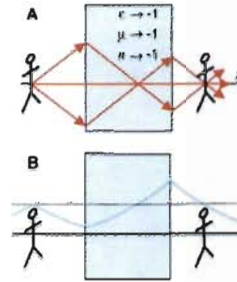
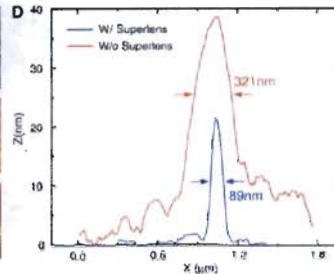
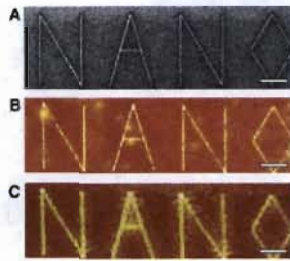
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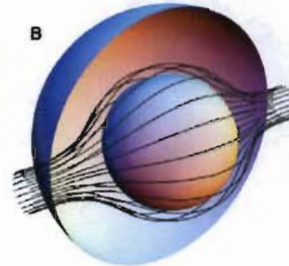
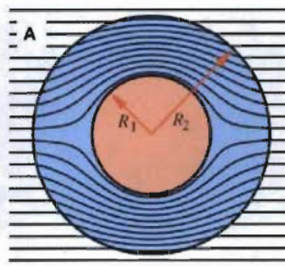
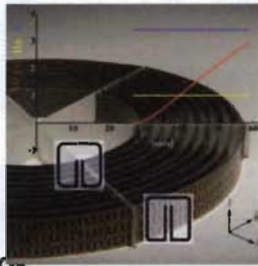


Emergent Phenomena in Metamaterials

Breaking the diffraction limits – superlens



Electromagnetic cloaking – transformation optics:



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NATIONAL LABORATORY
EST. 1943

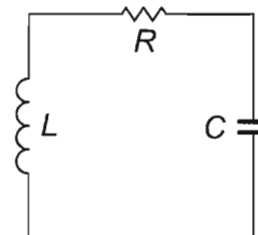
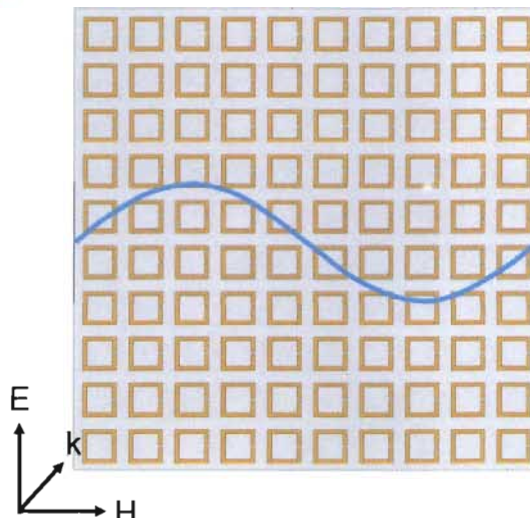
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Resonances in Split Ring Resonators



➤ Resonance frequency: $\omega^2 = \frac{1}{LC} - \frac{R^2}{4L^2}$

➤ Electromagneto effect in general

➤ Under normal incidence: purely electric response

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EST. 1943

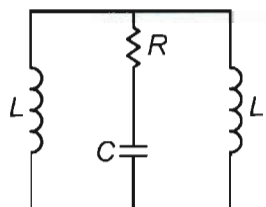
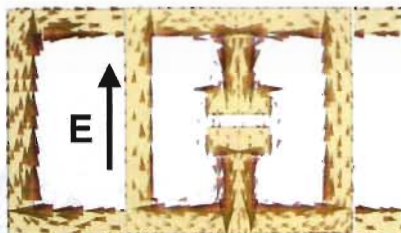
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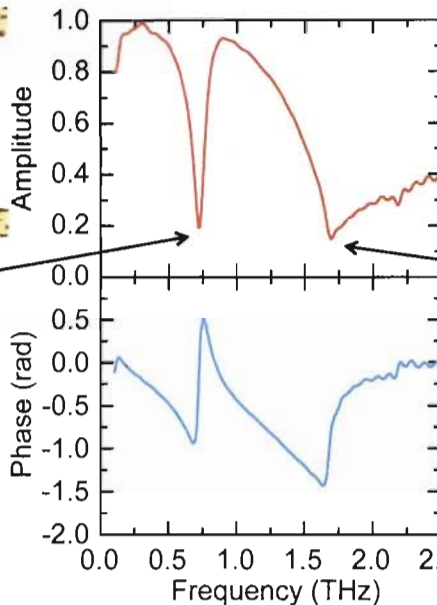
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Electric Resonant Resonance



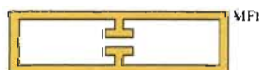
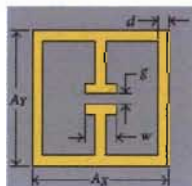
RLC resonance



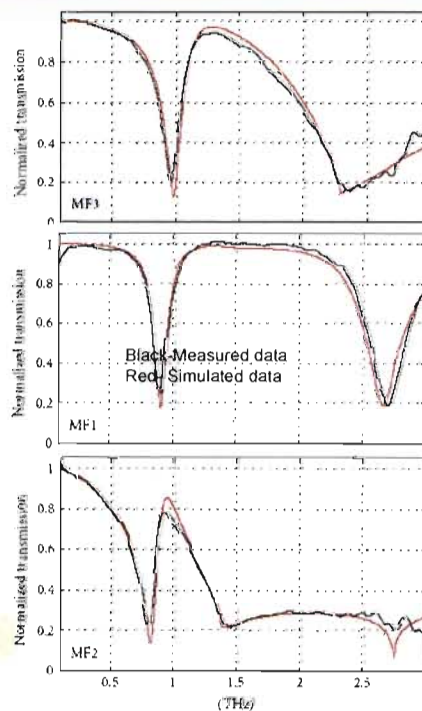
Collective dipolar resonance



Rectangular eSRR – Engineering Resonances



MF2

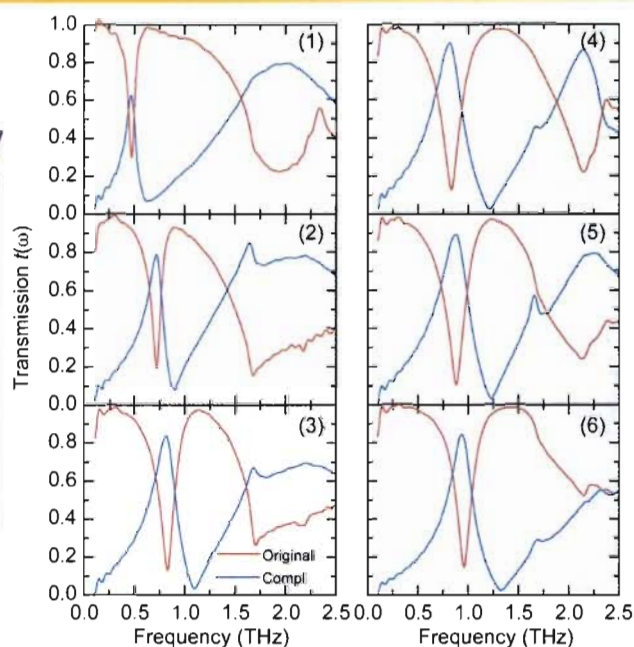
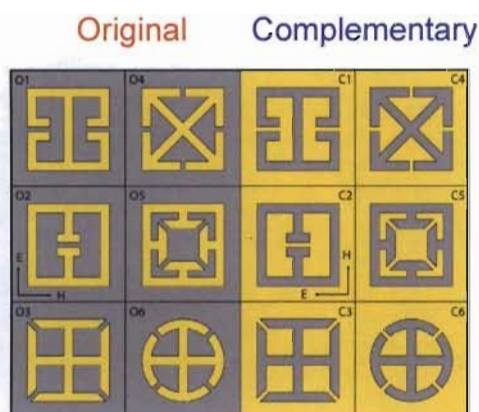


Azad et al., *Appl. Phys. Lett.* **92**, 011119 (2008).

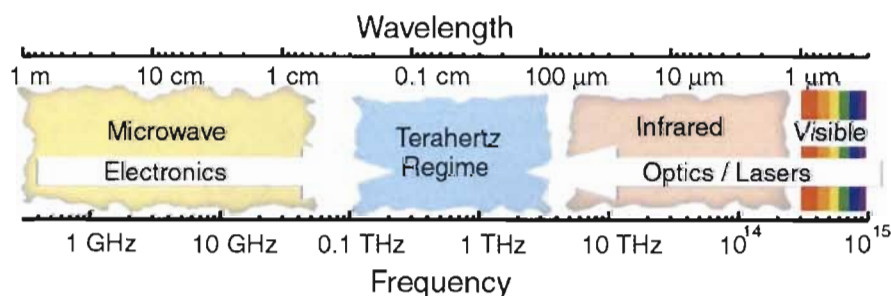


Complementary THz Electric Metamaterials

A series of electric SRRs:



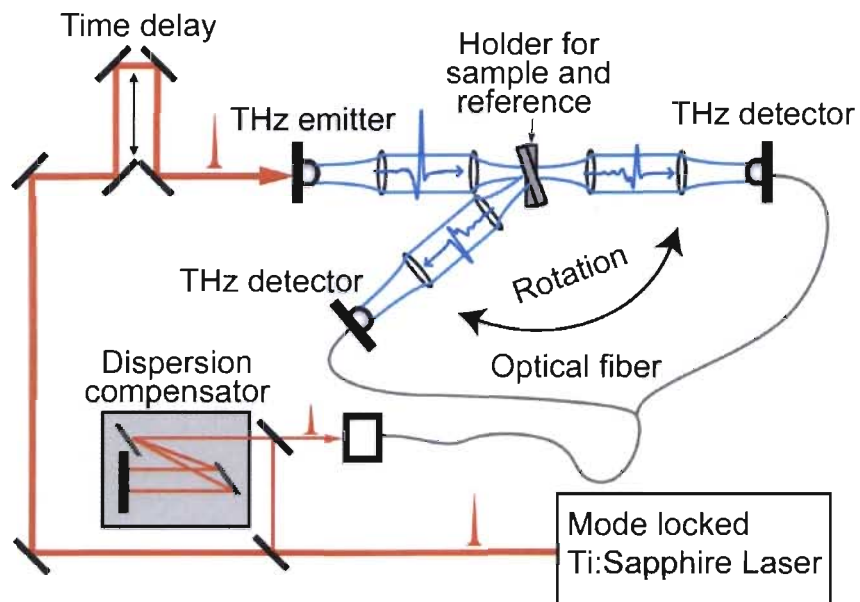
Why Terahertz Metamaterials?



- THz is one of the least developed and most challenging regimes in the electromagnetic spectrum
- Classical electronics and quantum photonics in general cannot be directly translated to the THz regime
- THz sources and detectors are limited
- Functional THz devices and components are not widely available



Terahertz Time-Domain Spectroscopy



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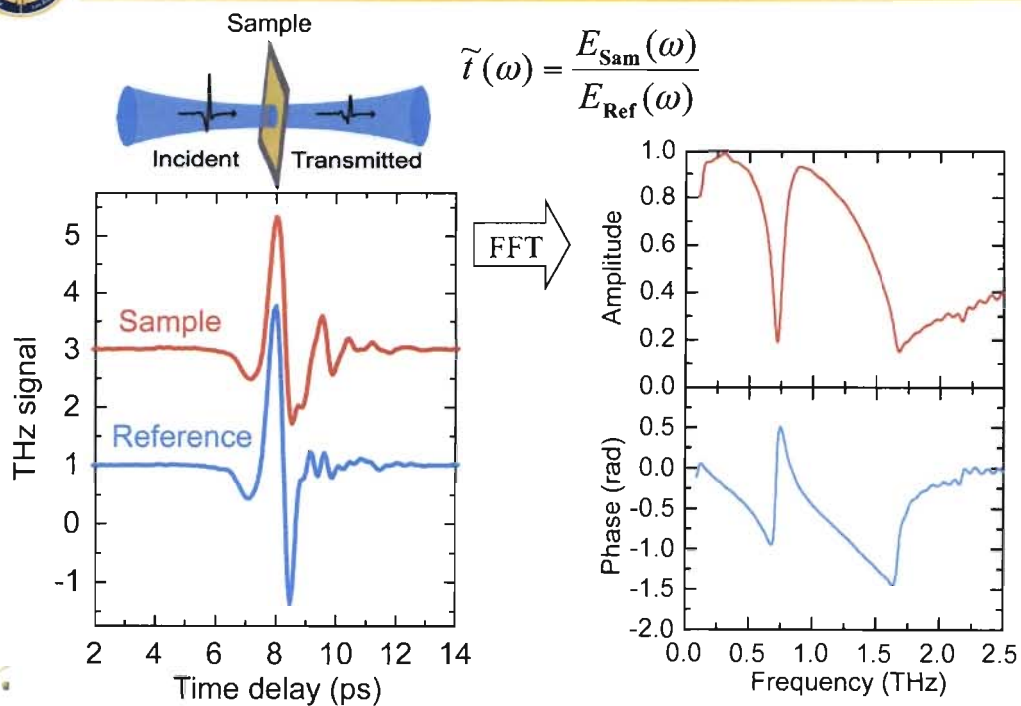
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Transmission and reflection, angular dependence

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Terahertz Time-Domain Spectroscopy

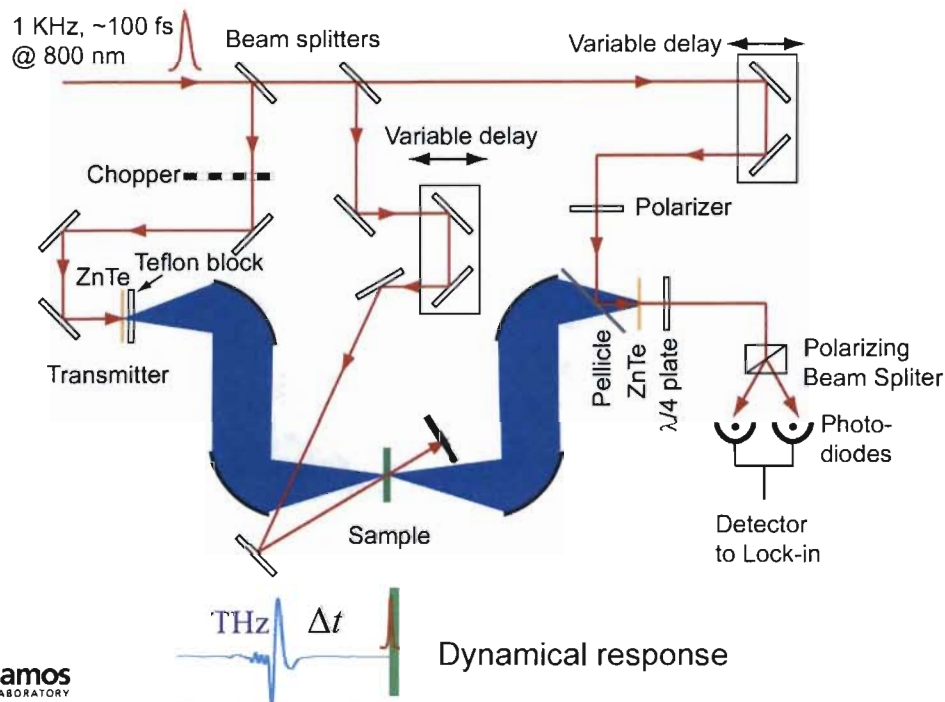


EST. 1941
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Optical-Pump Terahertz-Probe



Outline

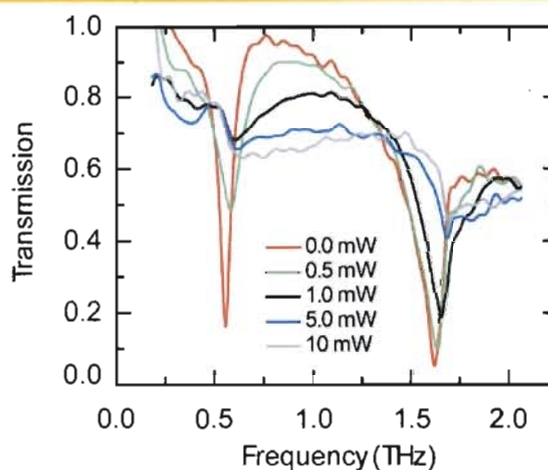
- ☐ Introduction
- ☒ **Actively and dynamically tunable THz metamaterials**
 - Hybrid semiconductor metamaterials
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Dynamically Switchable THz Metamaterials



photo-excitation



Performance:

- High efficiency with low fluence
- Ultrafast in Switching Off
- Slow in Switching Recovery



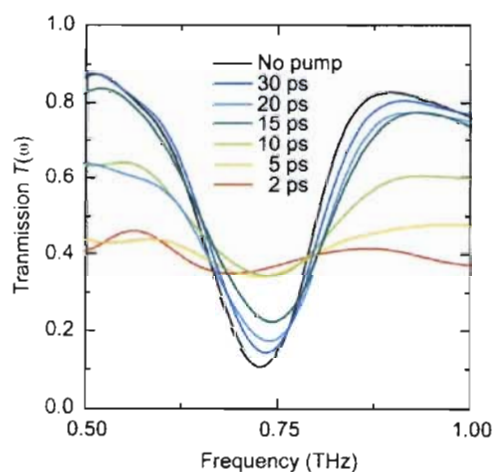
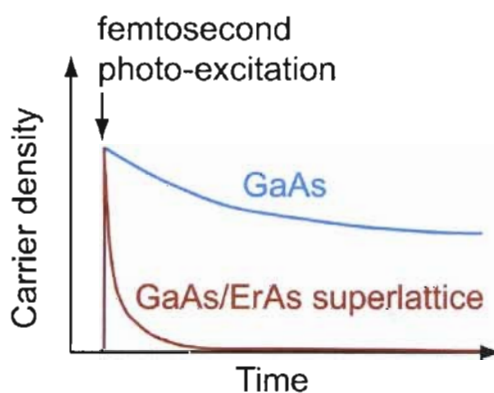
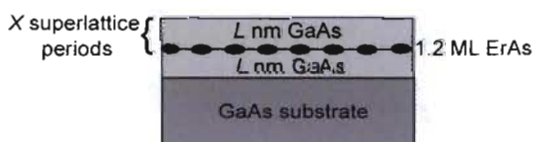
Padilla *et al.*, *Phys. Rev. Lett.* **96**, 107401 (2006).

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Ultrafast Dynamical Switching



Ultrafast switching recovery ~ 20 ps
(with carrier lifetime ~ 10 ps)



Chen *et al.*, *Opt. Lett.* **32**, 1620 (2007).

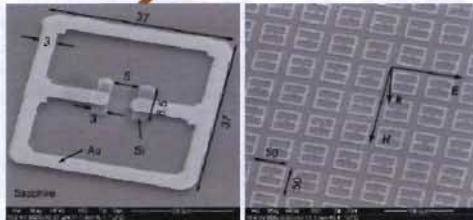
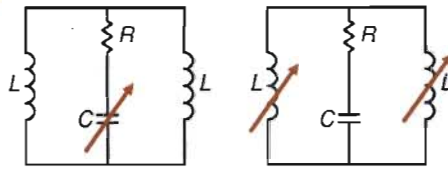
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Frequency Agile THz Metamaterials

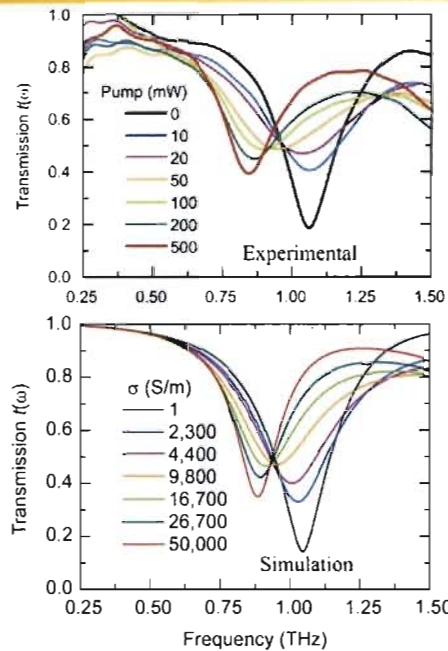


unit: μm



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Chen *et al.*, *Nature Photon.* **2**, 295 (2008).

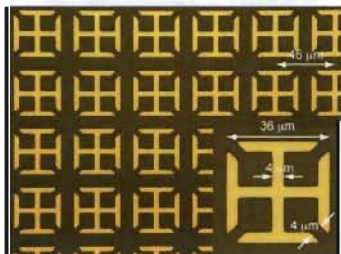


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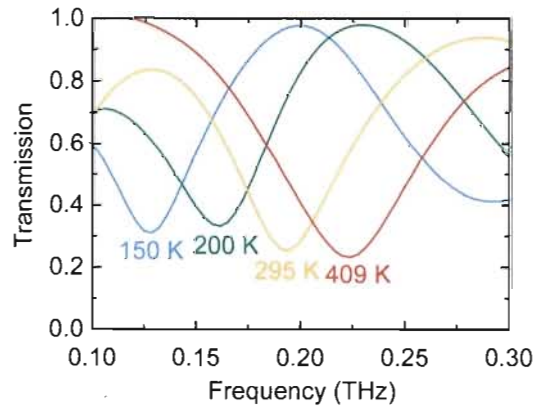
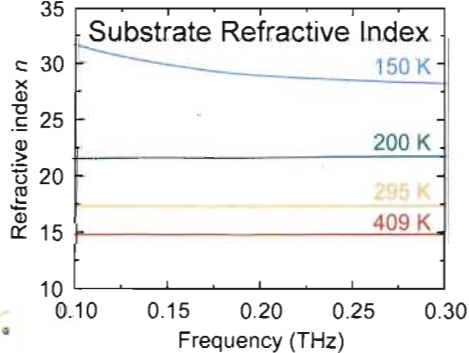


Thermally Tunable Terahertz Metamaterials

Strontium Titanate Substrate



$$\omega_0 = 1/\sqrt{LC} \sim 1/n$$



- Continuously frequency tuning
- No significant change in resonance strength

Singh *et al.*, *Opt. Lett.* in press (2011).

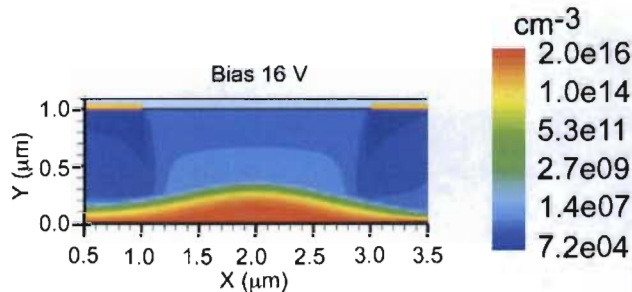
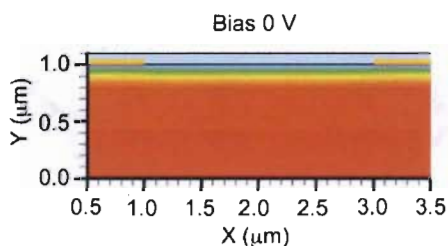
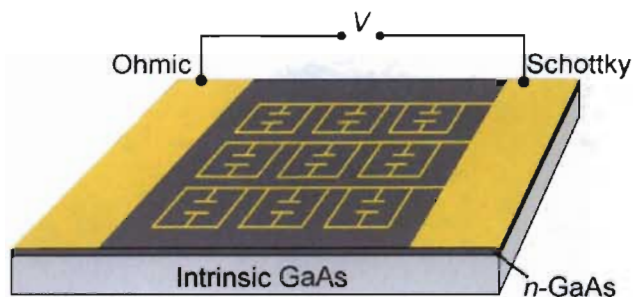
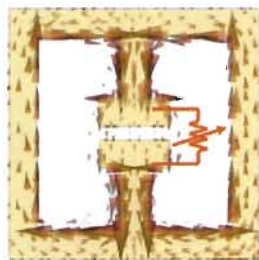
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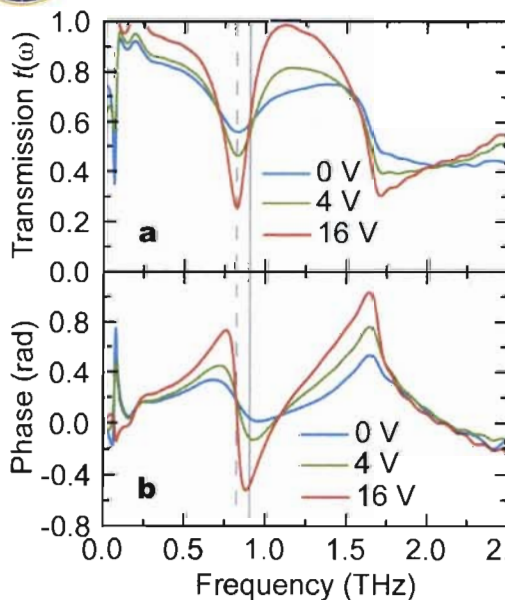




Electrically Switchable THz Metamaterials



Amplitude and Phase Modulations

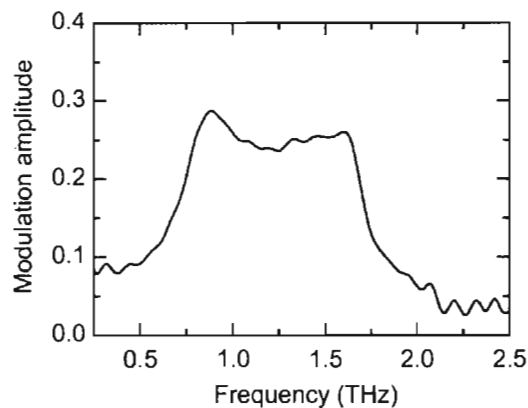
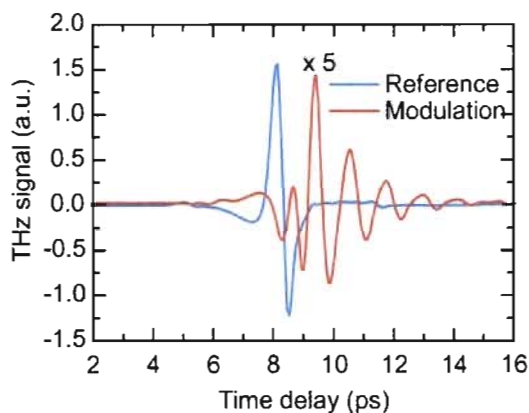


- Power modulation depth:
 $M = (T_{0V} - T_{16V}) / T_{0V} = 80\%$, or
amplitude modulation depth 55%
- Phase modulation $\Delta\phi = \pi/6$
- Amplitude and phase modulations are correlated
- In THz-TDS, both amplitude and phase modulations contribute to the modulation signal
- ✓ Broadband modulation

$$|\Delta \hat{t}(\omega)| = |t_{V1}(\omega)e^{i\phi_{V1}(\omega)} - t_{V2}(\omega)e^{i\phi_{V2}(\omega)}|$$



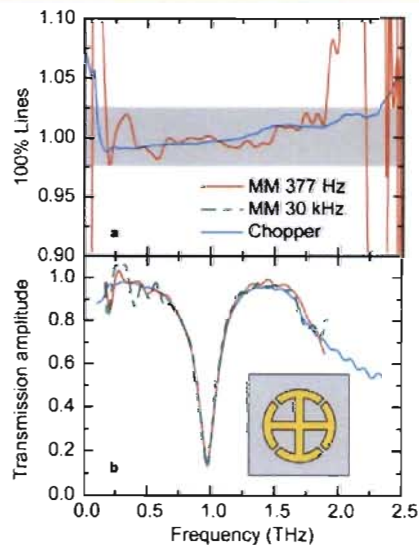
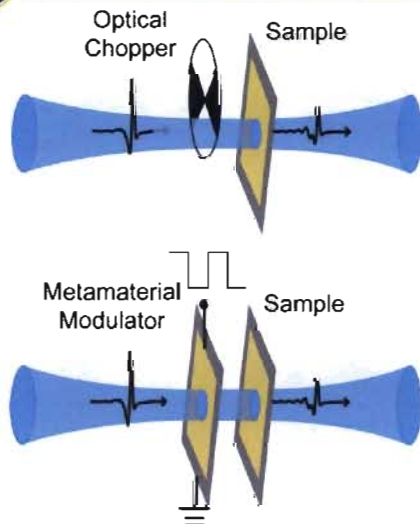
Broadband THz Modulation



Bandwidth: roughly between the two resonances



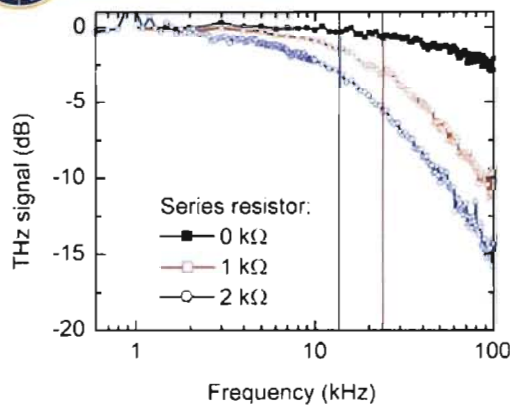
Serving as the Optical Chopper in THz-TDS



The metamaterial modulator is integrable, broadband, and high speed, without any moving part, room temperature operation



Fast Electrical Modulation of THz Waves



$$f = \frac{1}{2\pi RC}$$

Series resistance:

$R_{\text{Schottky}} = 126 \text{ ohm}$

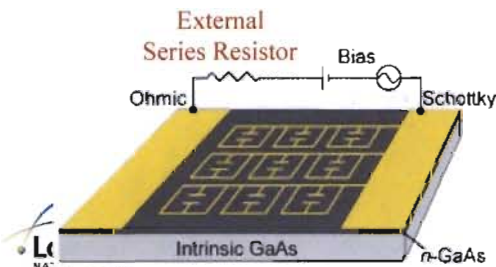
$R_{\text{Fgen}} = 50 \text{ ohm}$

$R_{\text{Series}} = 176 \text{ ohm}$

$$C_{\text{dep}} = A \left(\frac{qN_d\epsilon_s}{2(V_{bi} - V)} \right)^{1/2} = 8.9 \text{ nF @ 0 volt}$$

Solution: Connected with external series resistor

External series resistor	0 kΩ	1 kΩ	2 kΩ
Roll off frequency (Experimental)	100~200 kHz	24 kHz	14 kHz
Roll off frequency (Calculation)	101 kHz	15 KHz	8 kHz



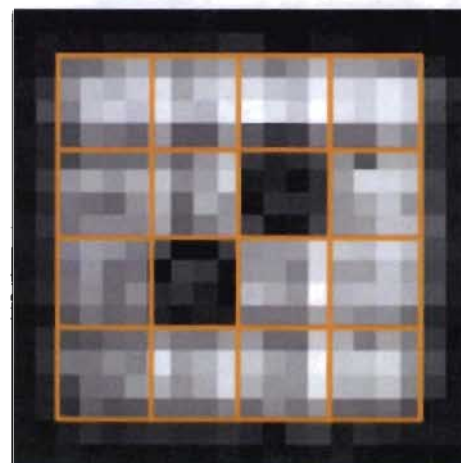
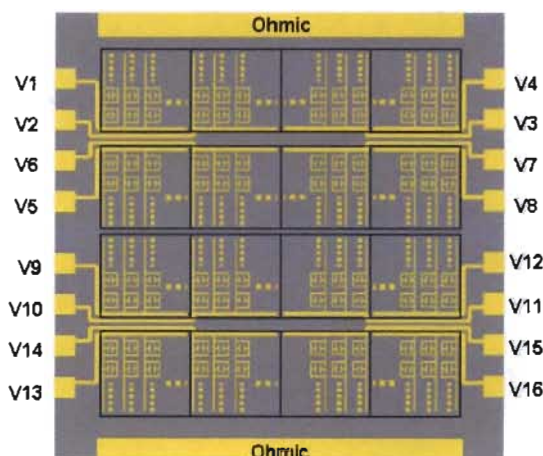
Chen *et al.*, *Appl. Phys. Lett.* **93**, 091117 (2008).

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NISA



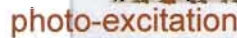
THz Metamaterial Spatial Modulator



4 × 4 pixels, each pixel is independently controlled by voltage bias



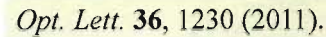
Optical Switch



PRL **96**, 107401 (2006); *Opt. Lett.* **32**, 1620 (2007).

Temperature Tuning

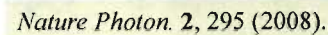
Strontium Titanate Substrate



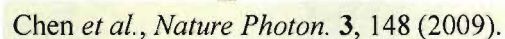
Electrical Switch



Optical Tuning

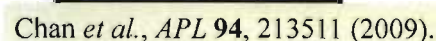


Broadband THz Modulator



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THz Spatial Light Modulator



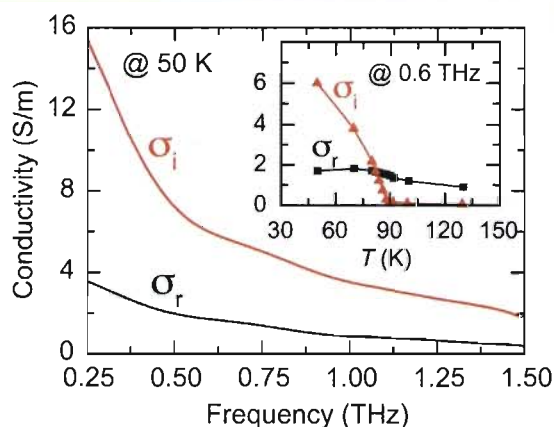
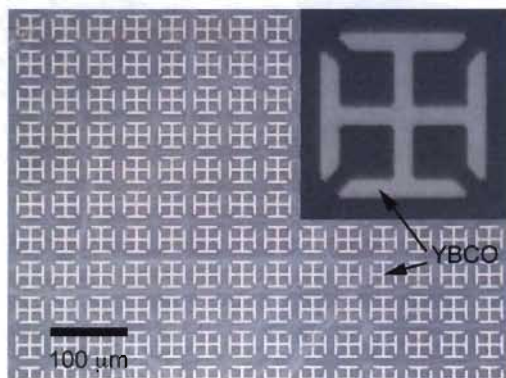


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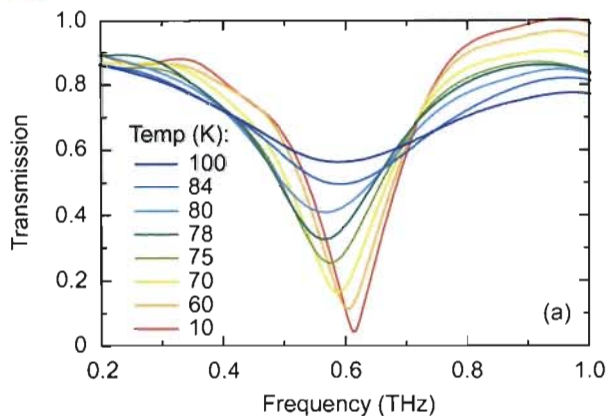
Temp-Dependent Complex Conductivity in HTS



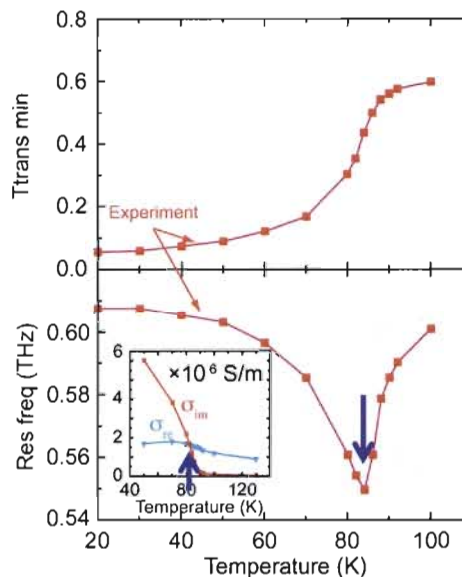
- HTS films: epitaxial YBCO films ($T_c \sim 90\text{K}$) by PLD
- Fabrication: photolithography and wet chemical etching
- High complex conductivity with $\sigma_i > \sigma_r$ at low temperatures
- Highly tunable conductivity at THz frequencies



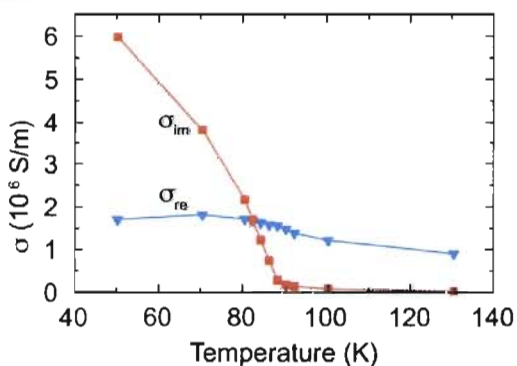
Thermally Tunable Metamaterial Resonance



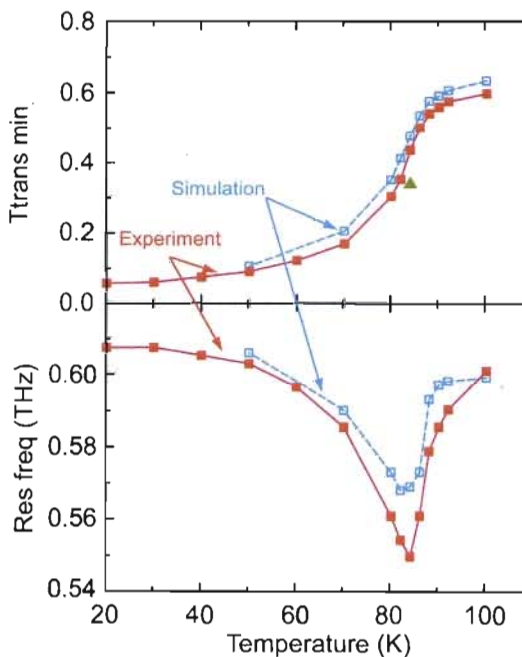
- Switching resonance strength
- Shifting resonance frequency
- Unique feature at $\sigma_i = \sigma_r$



Numerical Simulations



- Use experimental complex conductivity at 0.6 THz
- Finite-element numerical simulations using Comsol Multiphysics





LC Resonance in Superconducting SRRs

- Resonance frequency is given by: $\omega^2 = \frac{1}{LC} - \frac{R^2}{4L^2}$
- Total inductance $L = L_G + L_S$, where L_G is the loop inductance:

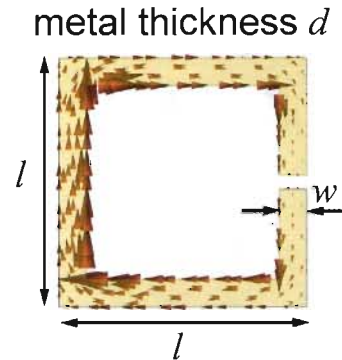
$$L_G = 0.02339 \left[2l \log \left(\frac{2l^2}{w+d} \right) - 2l \log(2.414l) \right] + 0.01016 [1.828l + 0.447(w+d)]$$

✓ l, w, d in inches, L_G in μH

✓ Additional (kinetic) inductance L_S from SRR superconductor strips

- Capacitance: $C = \frac{1}{L_G \omega_0^2}$

✓ Assuming perfect conductor with resonance frequency ω_0 through numerical simulations



SRR Resistance and Inductance

- Surface impedance: $\tilde{Z}_s = R_s - iX_s = Z_0 \frac{n_3 + i\tilde{n}_2 \cot \tilde{\beta}}{\tilde{n}_2^2 - n_3^2}$

$$\tilde{\beta} = \tilde{n}_2 d \omega / c_0 \quad \tilde{n}_2 = \sqrt{i\tilde{\sigma} / \epsilon_0 \omega} \quad \begin{array}{l} d: \text{film thickness} \\ \tilde{\sigma}: \text{film complex conductivity} \end{array}$$

Z_0 : vacuum impedance, n_3 : substrate index

- When $|\tilde{n}_2| \gg n_3$, it can be simplified as: $\tilde{Z}_s = i \frac{Z_0}{\tilde{n}_2} \cot \tilde{\beta}$

- By considering the non-uniform currents, the surface resistance of the SRR array is given by:

$$R = \frac{A}{w} R_s$$

A : loop circumference

w : SRR line width

R_s and X_s units: /square

- Kinetic inductance:

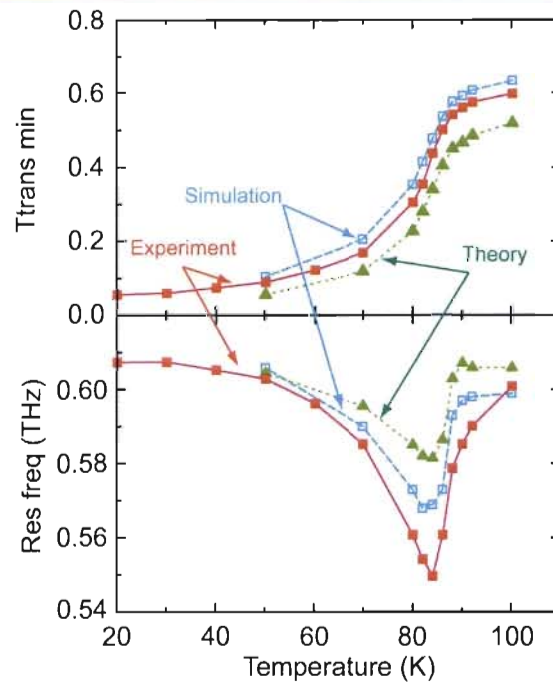
$$L_S = \frac{1}{\omega} \frac{A}{w} X_s$$



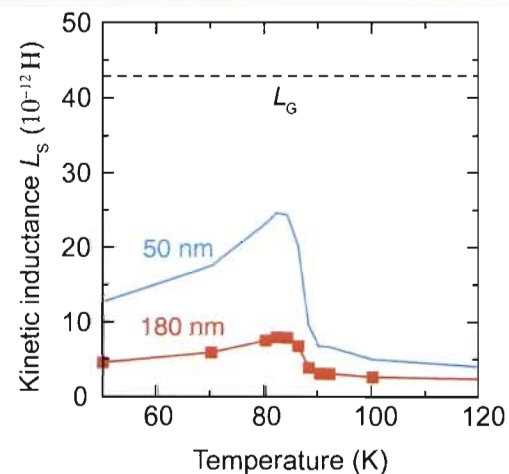
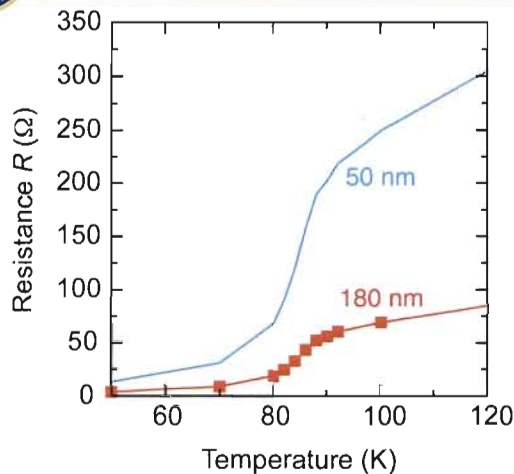
A Comparison: Exp, Sim, and Theory

$$\omega^2 = \frac{1}{(L_G + L_S)C} - \frac{R^2}{4(L_G + L_S)^2}$$

$$T_{\min} = \frac{(1 + n_3)R_S}{(1 + n_3)R_S + Z_0}$$



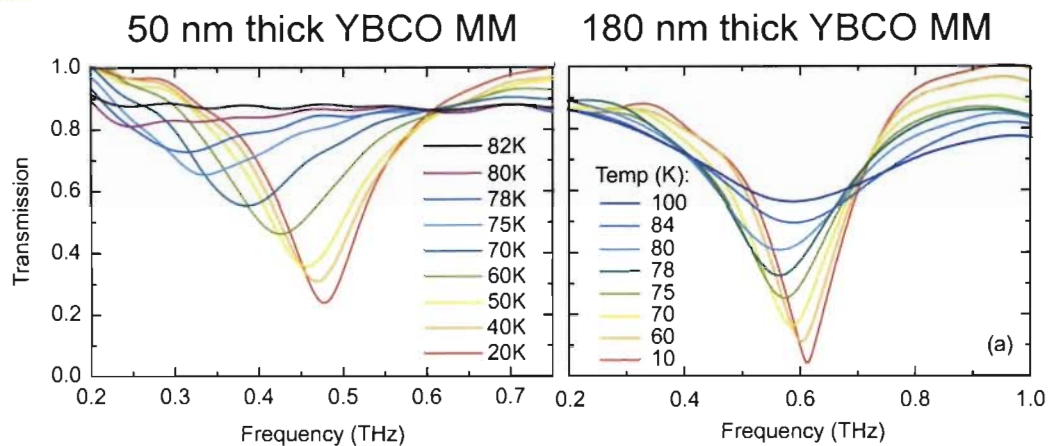
Thickness Dependent Surface Impedance



- Higher R indicates easier to switch the resonance.
- Higher L_S indicates lower resonance frequency
- Higher L_S indicates more resonance frequency shifting



Thickness Dependent Resonance Tuning

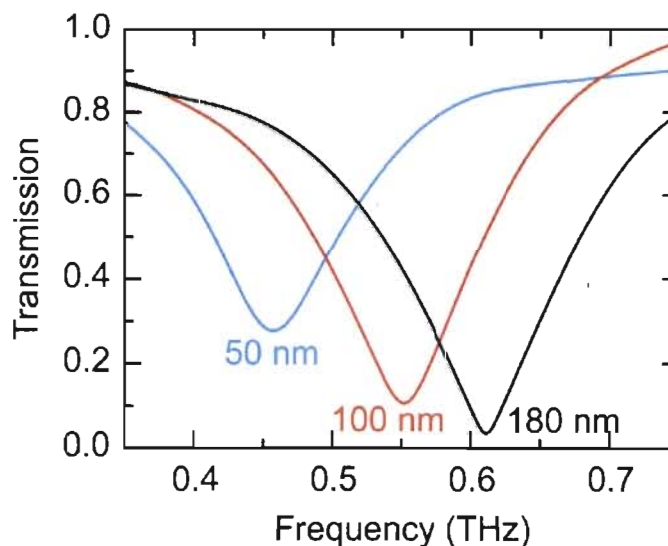


- 50 nm HTS MM is easier to switch off resonance
- Identical structure has a lower resonance frequency
- Resonance frequency tuning range is larger



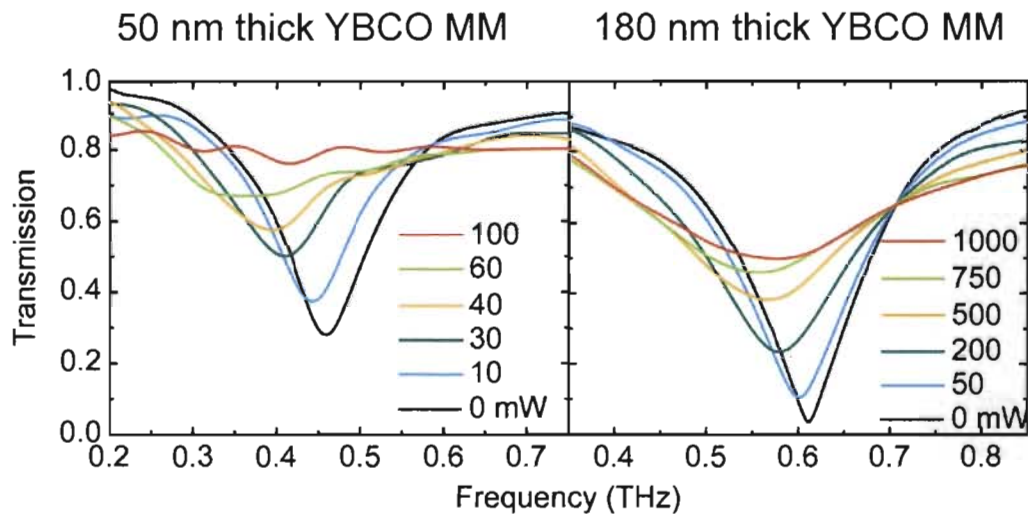
Thickness Dependent MM Resonance

Thinner HTS MMs result in a lower resonance frequency





Resonance Tuning by Photoexcitation



Similar behaviors as in temperature tuning

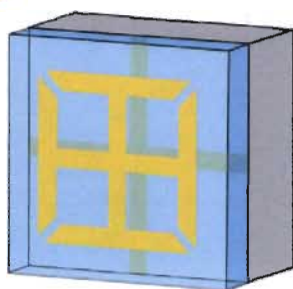


Outline

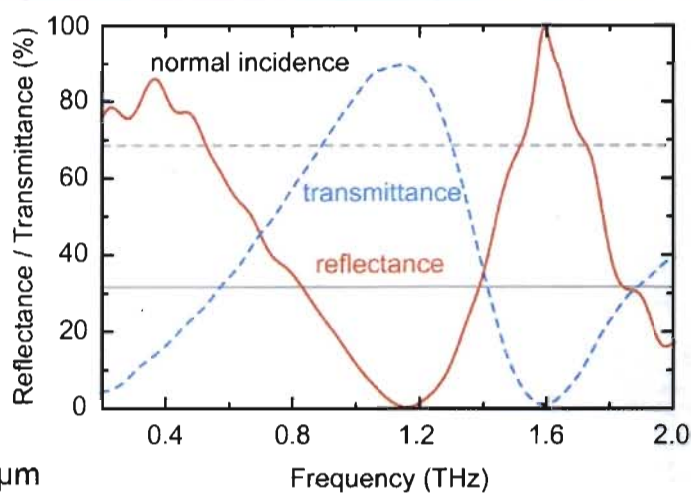
- ☐ Introduction
- ☐ Actively and dynamically tunable THz metamaterials
 - Hybrid semiconductor metamaterials
 - Tuning through photoexcitation, voltage, temperature
 - Device applications
- ☐ High temperature superconducting metamaterials
 - Temperature tuning
 - Optical tuning
 - Theoretical investigation
- ☐ Metamaterials as surface coatings
 - Antireflection coatings
 - Perfect absorbers
 - Theory
- ☐ Summary



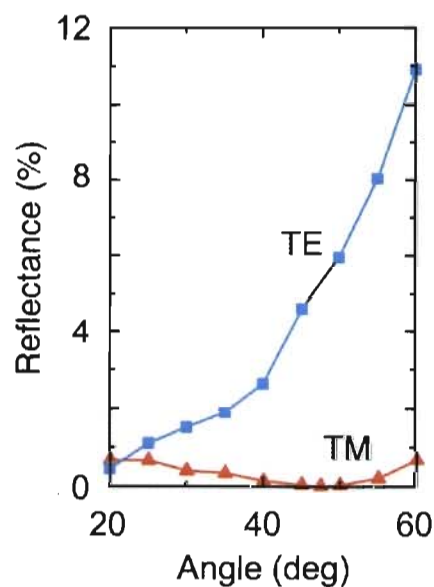
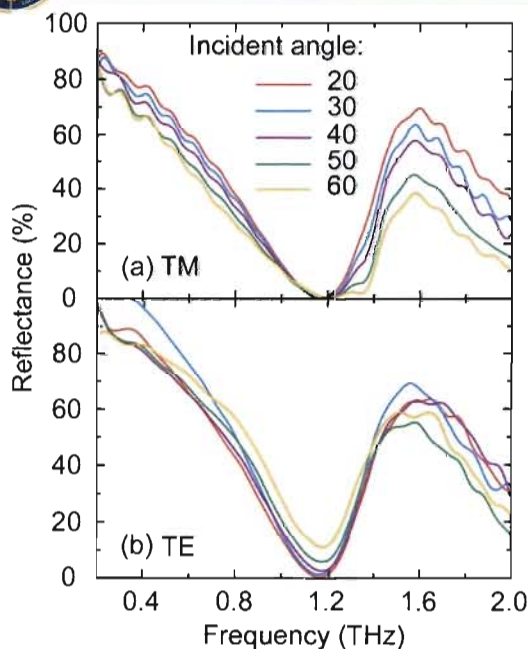
Metamaterial Antireflection Coating



- GaAs substrate
- Gold mesh
- Polyimide spacer $\sim 10 \mu\text{m}$
- Gold SRR
- Reflectance minimum 0.14%; Transmittance maximum $\sim 90\%$

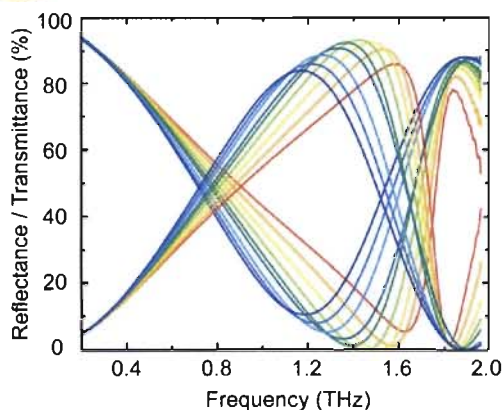


Angular-Dependent Anti-Reflection





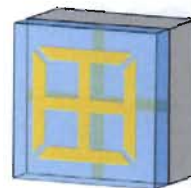
Numerical Simulations: Spacer Thickness



Simulation:

Substrate: $\epsilon_{\text{GaAs}} = 12.7$

MM spacer: $\epsilon_{\text{spacer}} = 1.5$



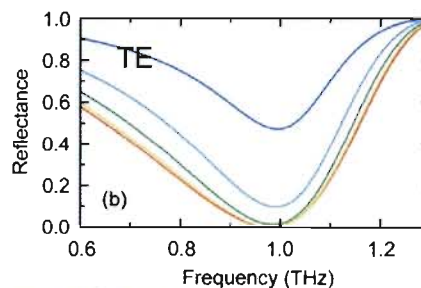
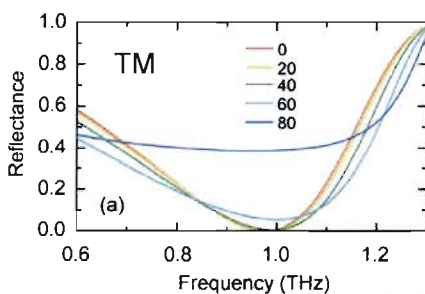
From red to blue:

Increasing the spacer thickness from $4 \mu\text{m}$ to $20 \mu\text{m}$

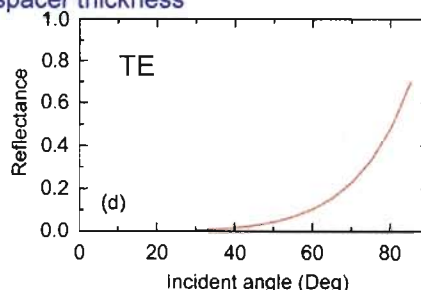
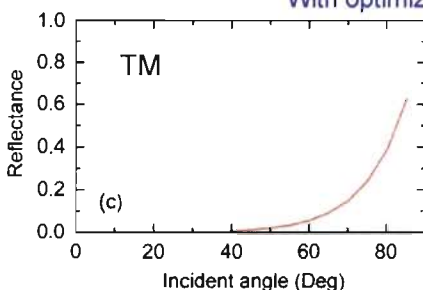
- With any dielectric constant of the spacer material, there is always a thickness achieving excellent antireflection, even the spacer dielectric constant is larger than the substrate
- The losses in metal and the spacer material mainly affect the transmittance, but has little effect on the reflectance



Numerical Simulations: Angular Dependence

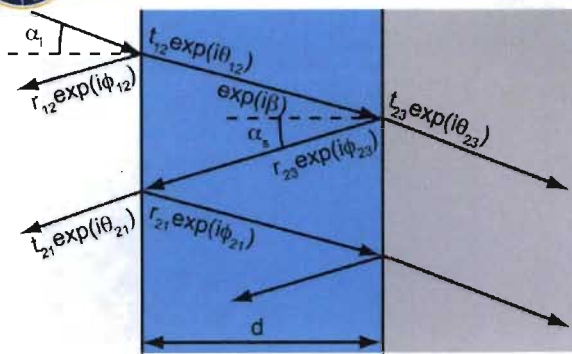


With optimized spacer thickness





Antireflection Mechanism



air SRR spacer mesh GaAs air SRR spacer mesh GaAs

$$\tilde{r} = \frac{r_{12}e^{i\phi_{12}} - r_{12}r_{21}r_{23}e^{i\zeta_1} + t_{12}r_{23}t_{21}e^{i\zeta_2}}{1 - r_{21}r_{23}e^{i(\phi_{21} + \phi_{23} + 2\beta)}}, \quad \zeta_1 = \phi_{12} + \phi_{21} + \phi_{23} + 2\beta$$

$$\tilde{t} = \frac{t_{12}t_{23}e^{i(\theta_{12} + \theta_{23} + \beta)}}{1 - r_{23}r_{21}e^{i(\phi_{23} + \phi_{21} + 2\beta)}}, \quad \zeta_2 = \theta_{12} + \phi_{23} + \theta_{21} + 2\beta$$

$$\beta = -\sqrt{\epsilon_{\text{spacer}}}k_0d/\cos(\alpha_s)$$



Chen *et al.*, *Phys. Rev. Lett.* **105**, 073901 (2010).

Operated by Los Alamos National Security, LLC for NNSA

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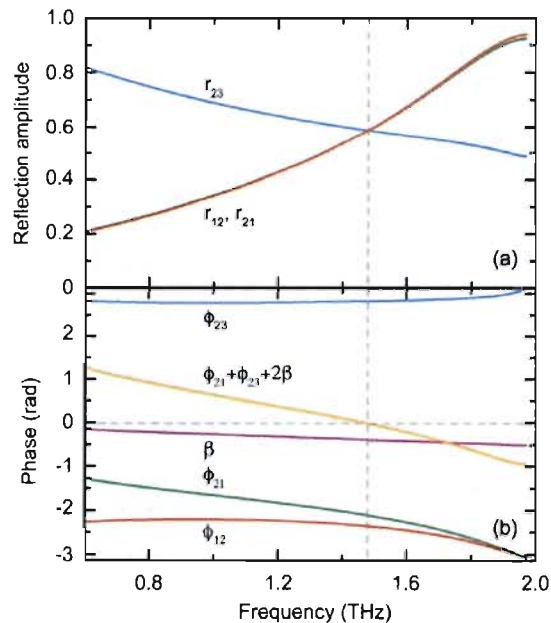
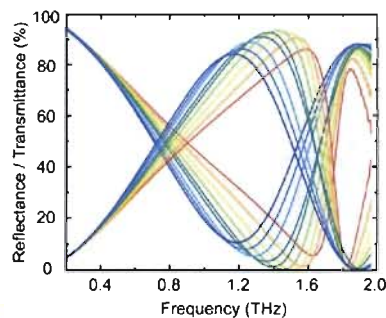
Antireflection Mechanism: Modeling Results

- Antireflection requirements:

$$r_{12} = r_{21} = r_{23},$$

$$\phi_{21} + \phi_{23} + 2\beta = 2m\pi$$

- Varying β (spacer thickness) reproduces the thickness dependent reflection and transmission



Chen *et al.*, *Phys. Rev. Lett.* **105**, 073901 (2010).

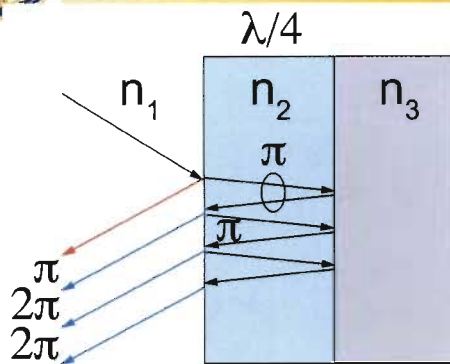
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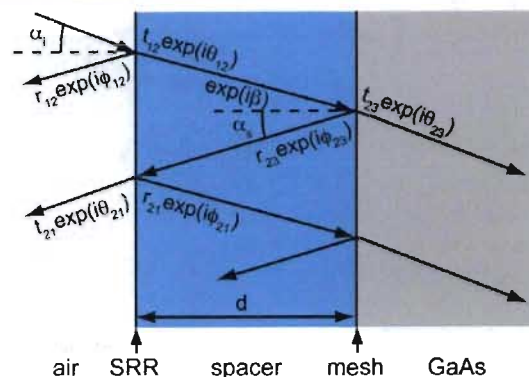




Comparison to Quarter-Wave Antireflection



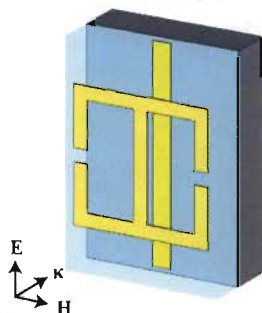
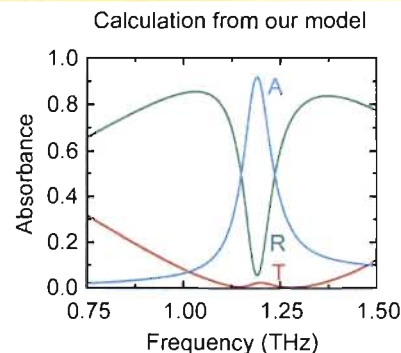
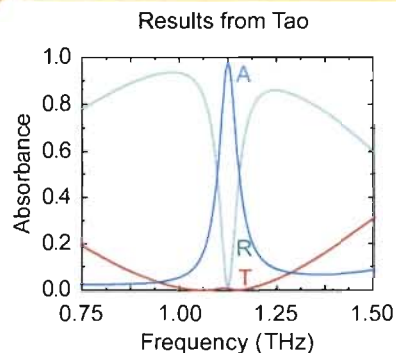
- $n_2 = (n_1 n_3)^{1/2} \rightarrow r_{12} = r_{21} = r_{23}$
- Phase difference π between direction reflection and second reflection
- Phase difference 2π in the following reflections



- At antireflection frequency $r_{12} = r_{21} = r_{23}$
- $\theta_{12} + \phi_{23} + \theta_{21} + 2\beta - \phi_{12} = \pi$ between direction reflection and second reflection
- $\phi_{21} + \phi_{23} + 2\beta = 0$ in the following reflections



Perfect Metamaterial Absorbers



The claimed magnetic response plays NO significant role in impedance matching

Landy *et al.*, *Phys. Rev. Lett.* **100**, 207402 (2008).
Tao *et al.*, *Opt. Express* **16**, 7121 (2008).
Chen *et al.*, *Phys. Rev. Lett.* **105**, 073901 (2010).



Summary

- Actively and dynamically tunable metamaterials will contribute to the development of THz science and technology
- We Investigated resonance switching and tuning in high temperature superconducting THz metamaterials by varying temperature and photoexcitation
- We also investigated metamaterials as THz antireflection coatings and perfect absorbers
- In both investigations we achieved reasonable level understanding of the underlying physics



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Collaborators:

LANL: Toni Taylor, Abul Azad, John O'Hara, Quanxi Jia, Stuart Trugman, Ranjan Singh, Jiangfeng Zhou, Matt Reiten, Dibakar Chowdhury

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Boston College: Willie Padilla

UCSB: Arthur Gossard

SNL: Igal Brener, Mark Lee, Michael Cich

Rice: Daniel Mittleman

Duke Univ: David Smith, Nan Jokest

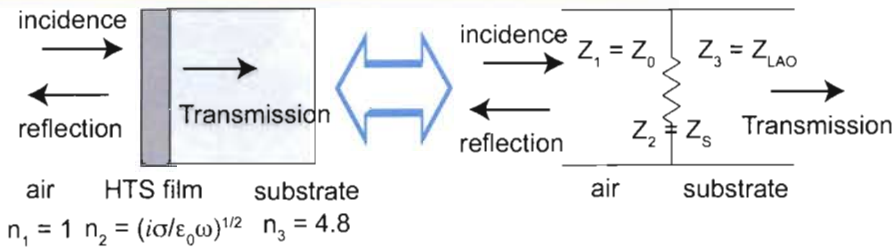
OSU: Weili Zhang

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Surface Impedance of HTS Film



- First calculate the reflection (transmission) coefficient of the HTS film

$$\tilde{r} = re^{i\phi} = \frac{\tilde{r}_{12} + \tilde{r}_{23}e^{i2\beta}}{1 + \tilde{r}_{12}\tilde{r}_{23}e^{i2\beta}} \quad \tilde{\beta} = \tilde{n}_2 d \omega / c_0$$

d is the film thickness

- Then calculate the reflection (transmission) coefficient of the TL

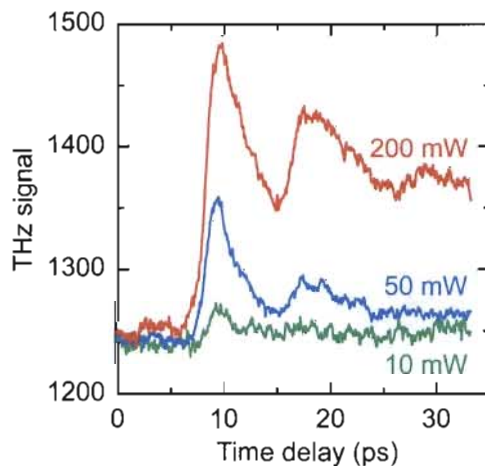
$$\tilde{r} = \frac{Z_1 - Z_2 // Z_3}{Z_1 + Z_2 // Z_3} = \frac{Z_1 Z_2 + Z_1 Z_3 - Z_2 Z_3}{Z_1 Z_2 + Z_1 Z_3 + Z_2 Z_3}$$

- The two reflection coefficients are equal, we can calculate Z_2

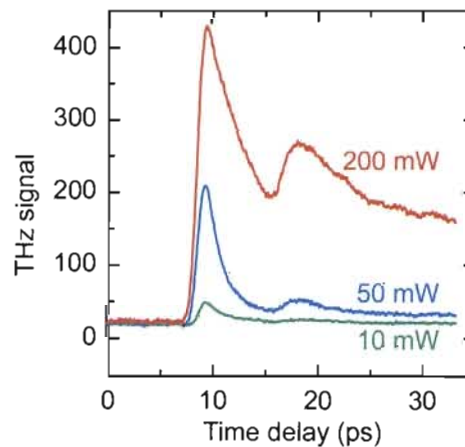


Ultrafast Dynamics

50 nm HTS metamaterial



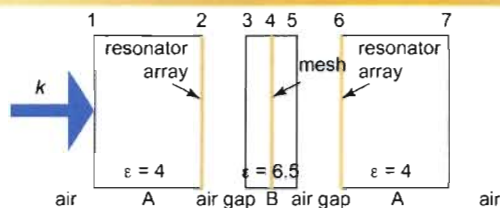
50 nm unpatterned HTS film



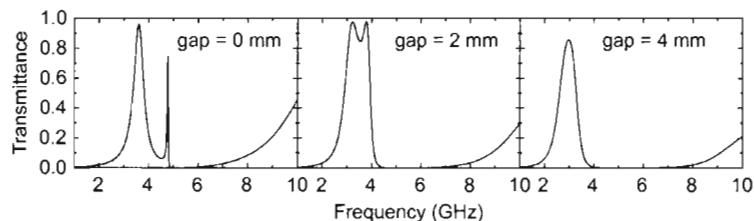
The “bumps” are due to multiple reflection inside the substrate, results in multiple photoexcitation.



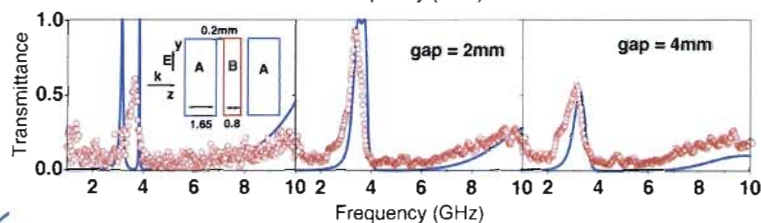
Electromagnetic-Wave Tunneling



We calculate each interface the reflection and transmission coefficients, then calculate the total reflection and transmission



Calculated results from our model



Experimental and simulation results from Zhou